

Managing Electrical Reliability During Layout Implementation

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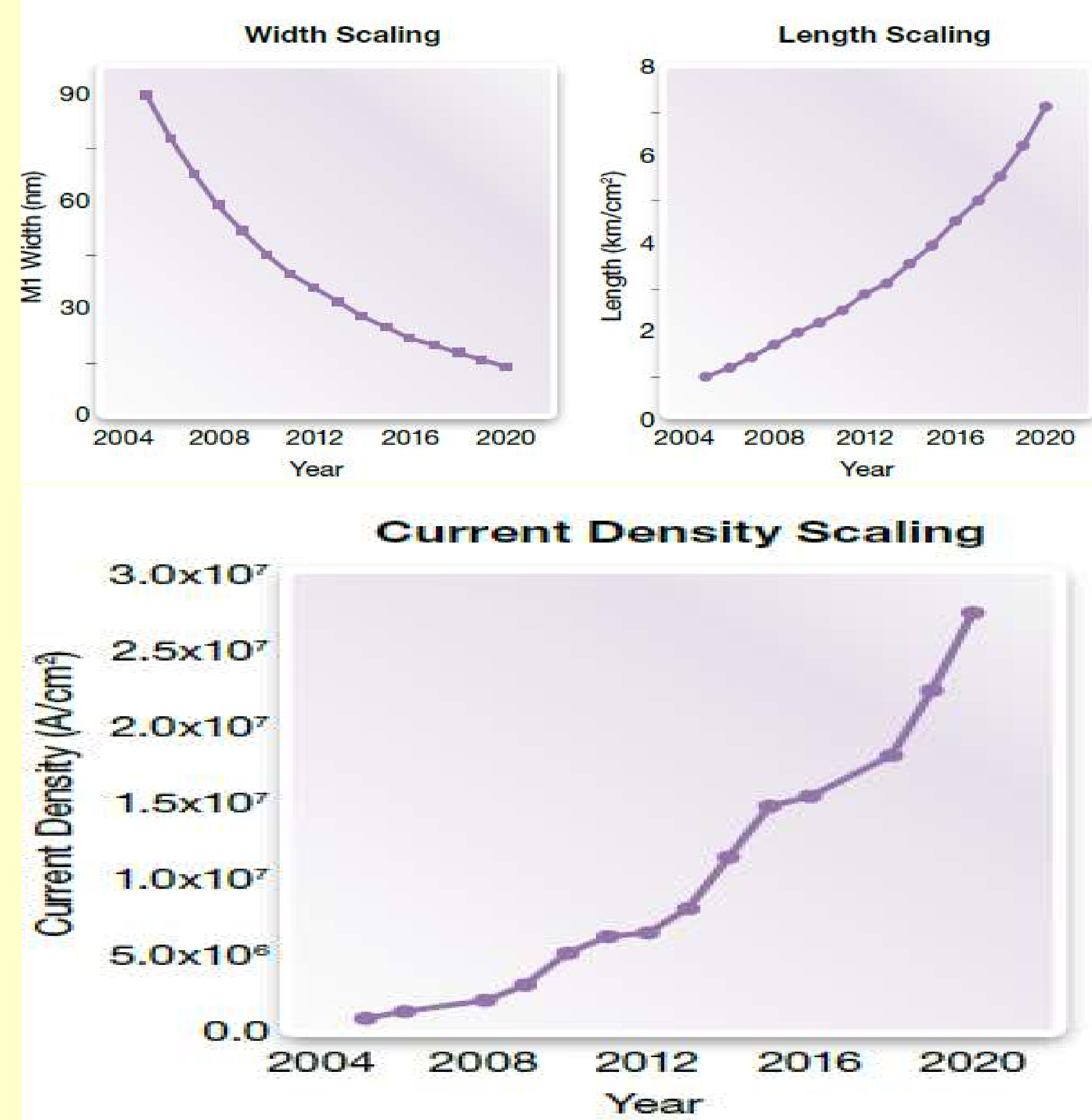


[1]- STMicroelectronics [2]-Cadence Design Systems

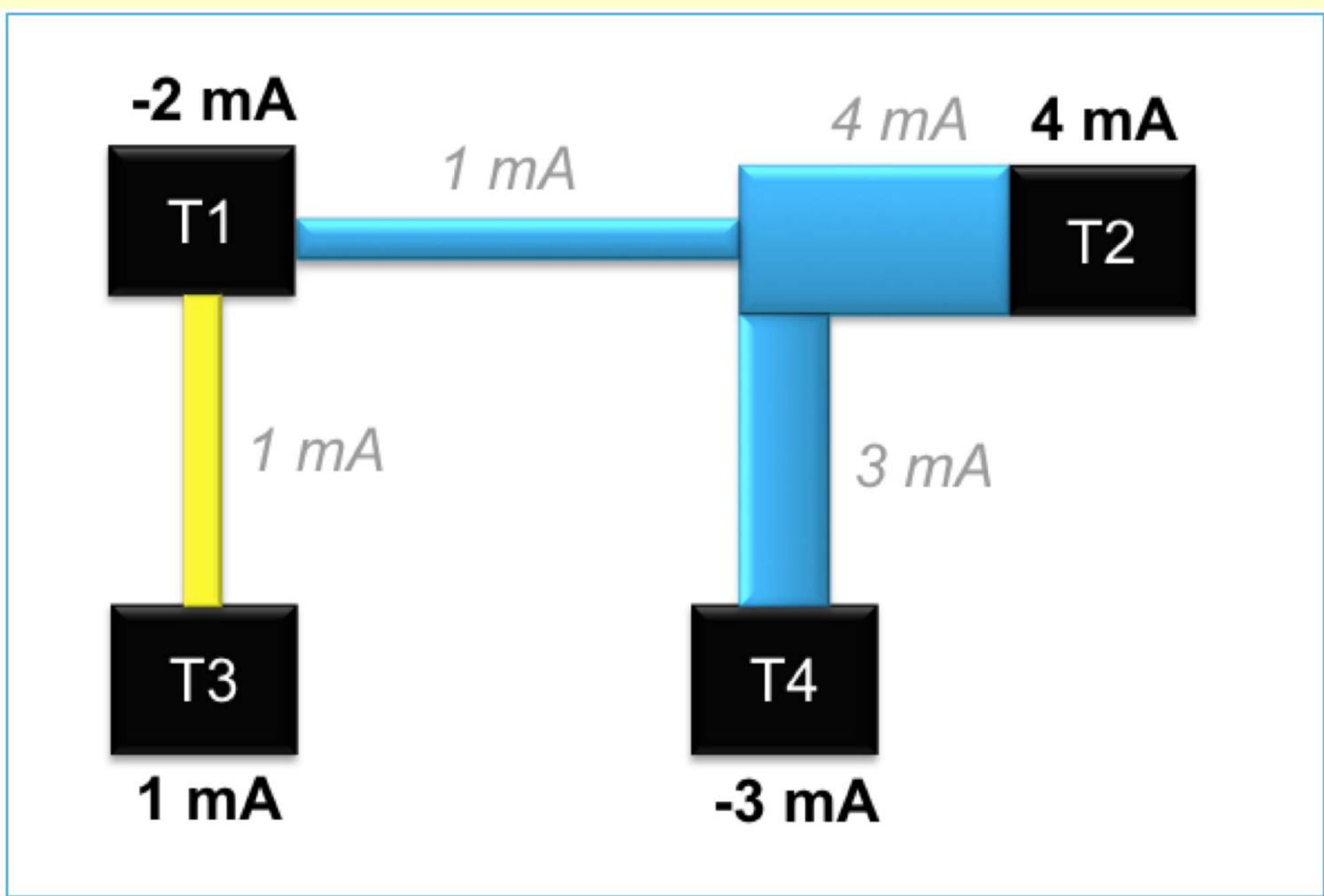


MOTIVATION

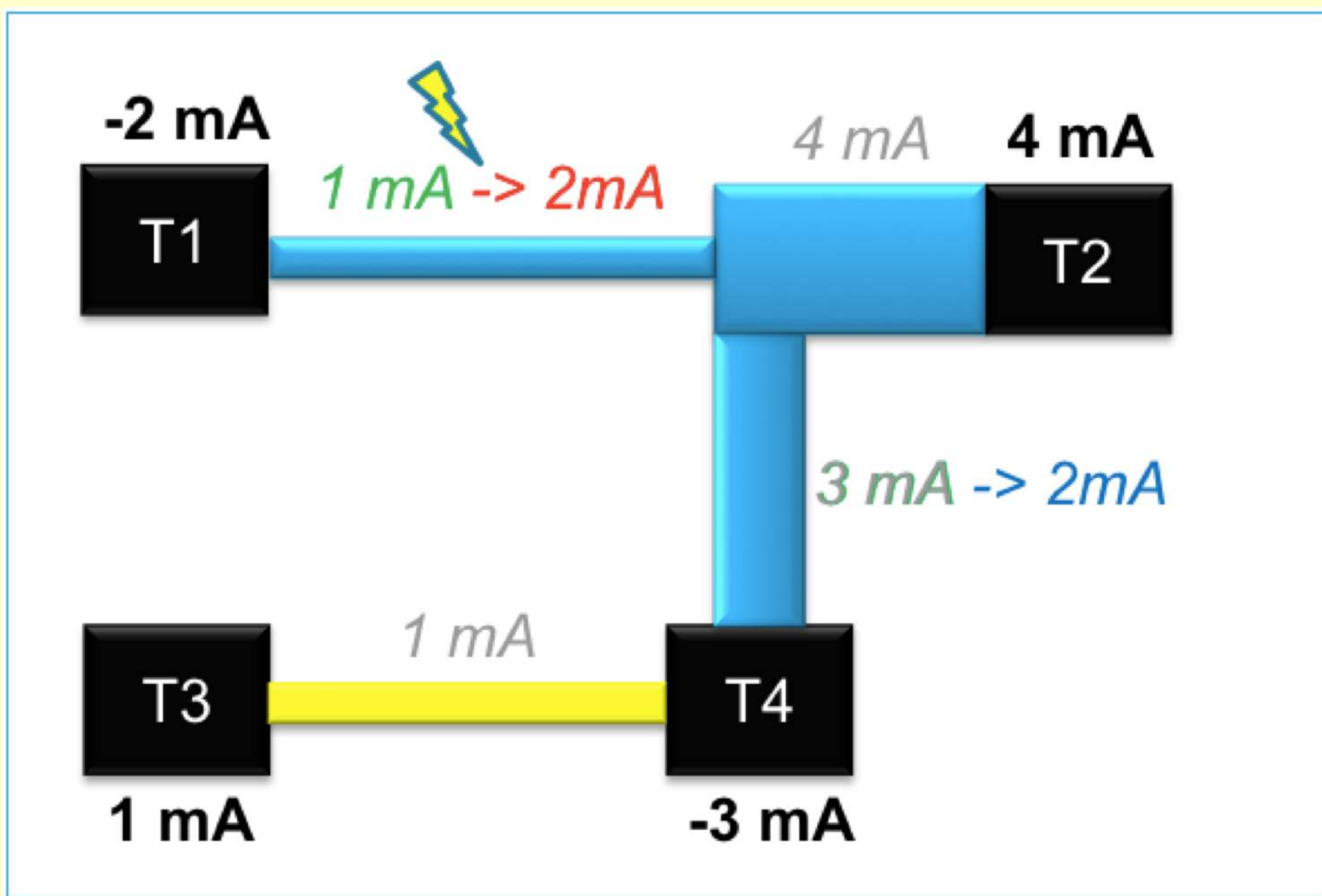
- Tight Failure Rate Specification** : 1ppm for Automotive and Industrial Application
- Power Hungry IP and SOC** : Demand of high speed application products in lower technology nodes is leading to increase in current density.
- Technology** : Graphs show the impact on metal dimensions and current density with technology shrinkage.
- Cost** : Reducing Metal Mask, to make product more competitive



- Need of knowing current topology during layout phase** to avoid EM-IR and design iterations

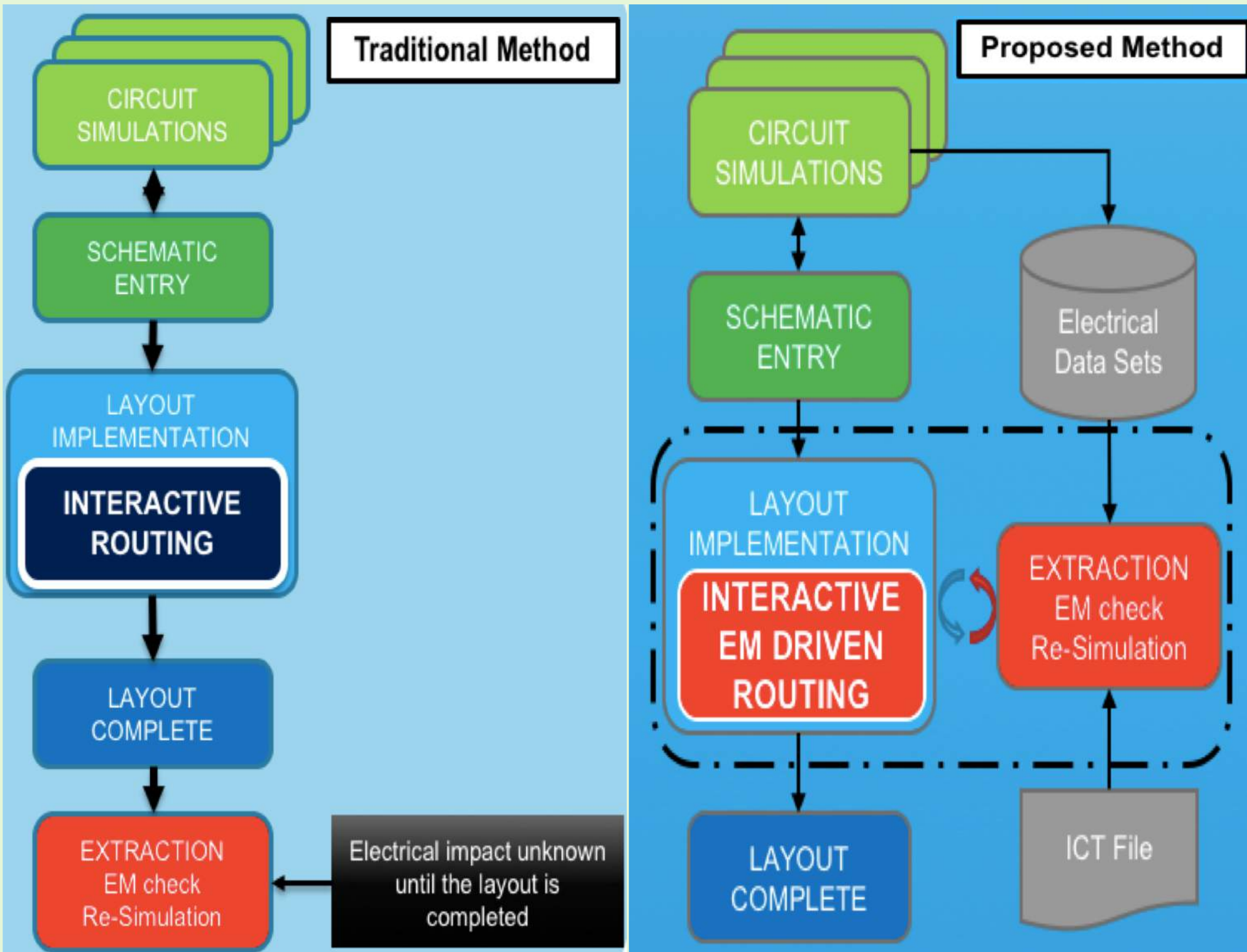


- We need the final topology** to be able to estimate the current going through all wires

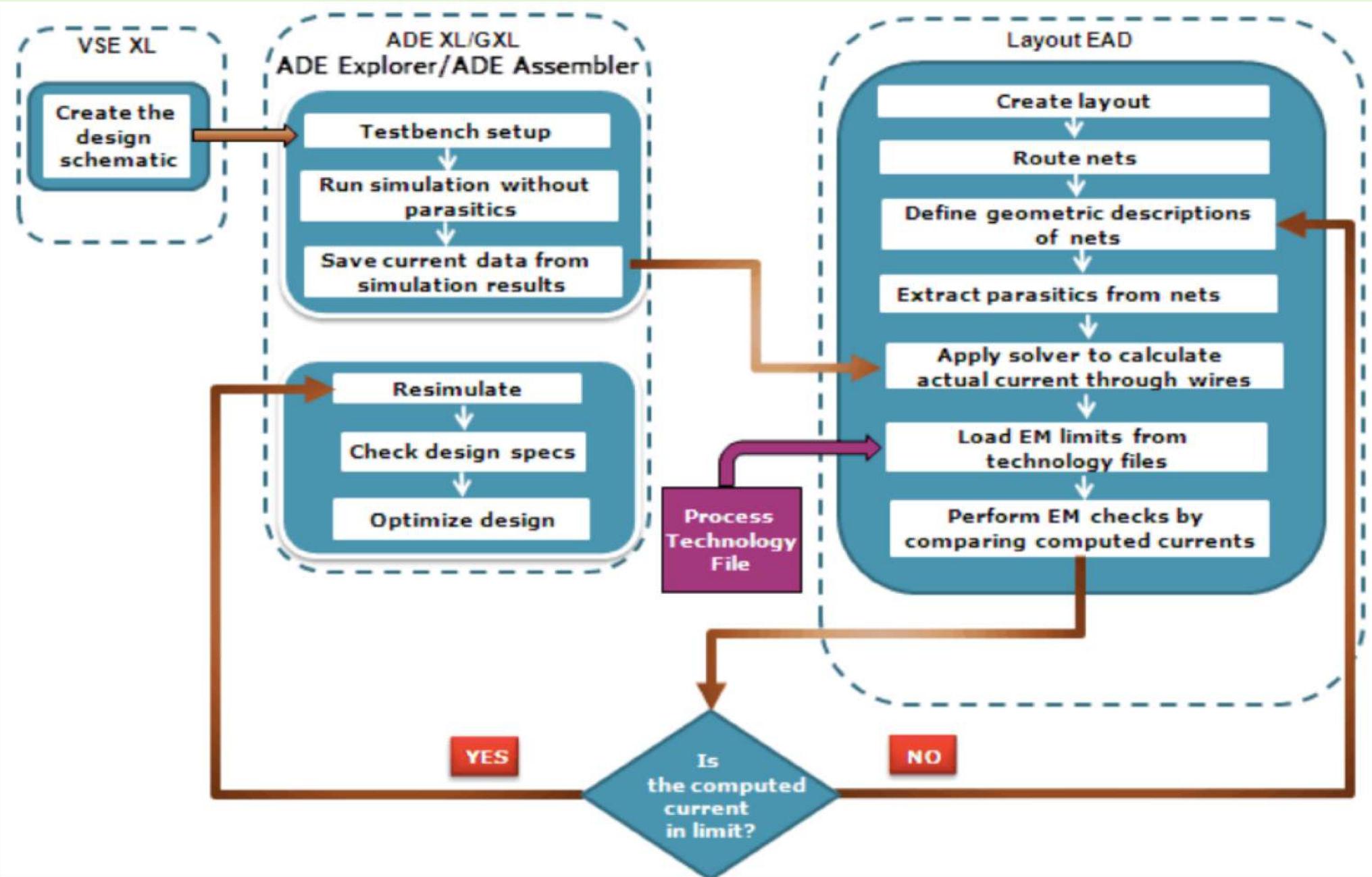


The proposed flow assists the user to achieve what he wants, while taking into account current density information

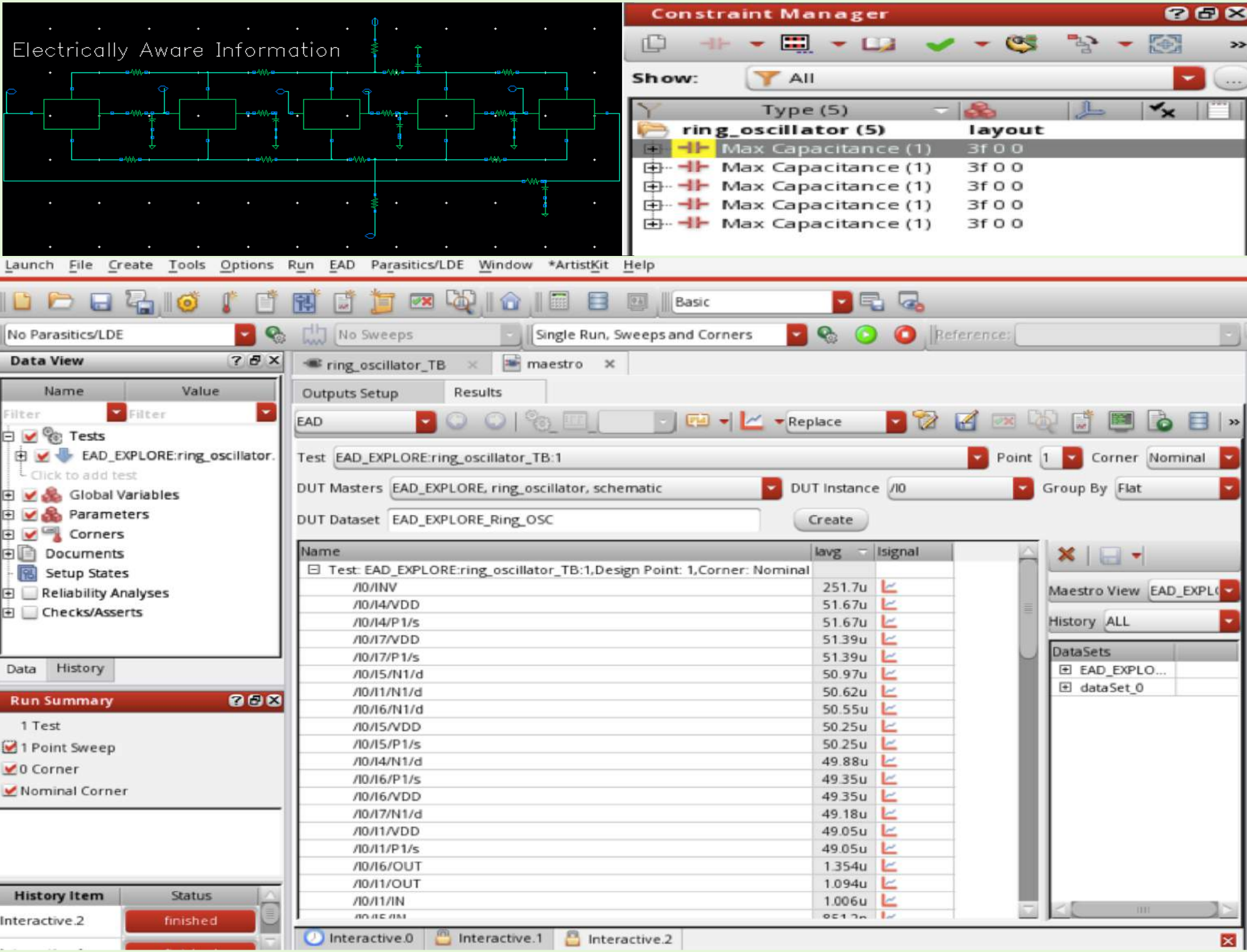
METHODOLOGY



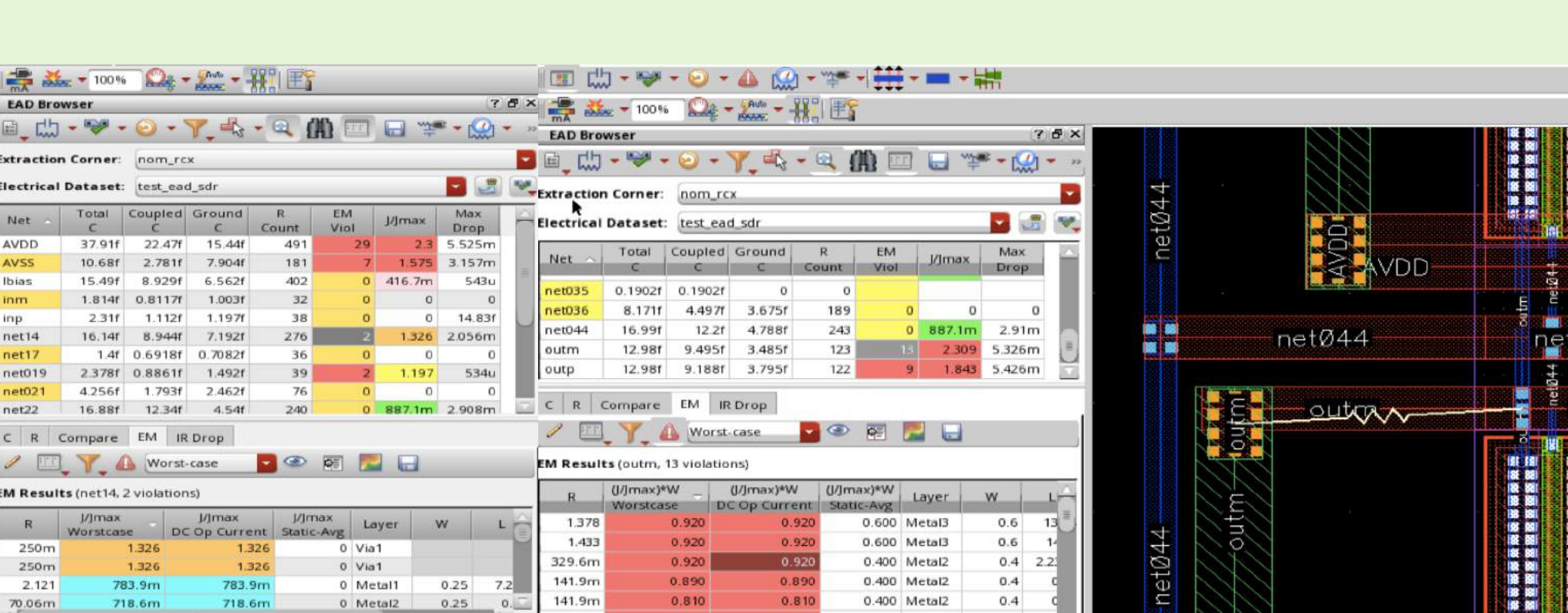
- Post Edit Parasitics (RC) and EM/IR check**, allows designer to check parasitics immediately after route is finished, using Virtuoso EAD without waiting till LVS or signoff
- During interactive routing step** of the layout implementation the electromigration constraints are taken into account. It decreases the number of iterations.
- Simulation current driven interactive routing**, allows designer to draw a net wire interactively with the width required to meet EM for peak current, using Virtuoso SDR
- Early EM optimize design** and verify the performance and reliability
- Reducing signoff time** and design iterations



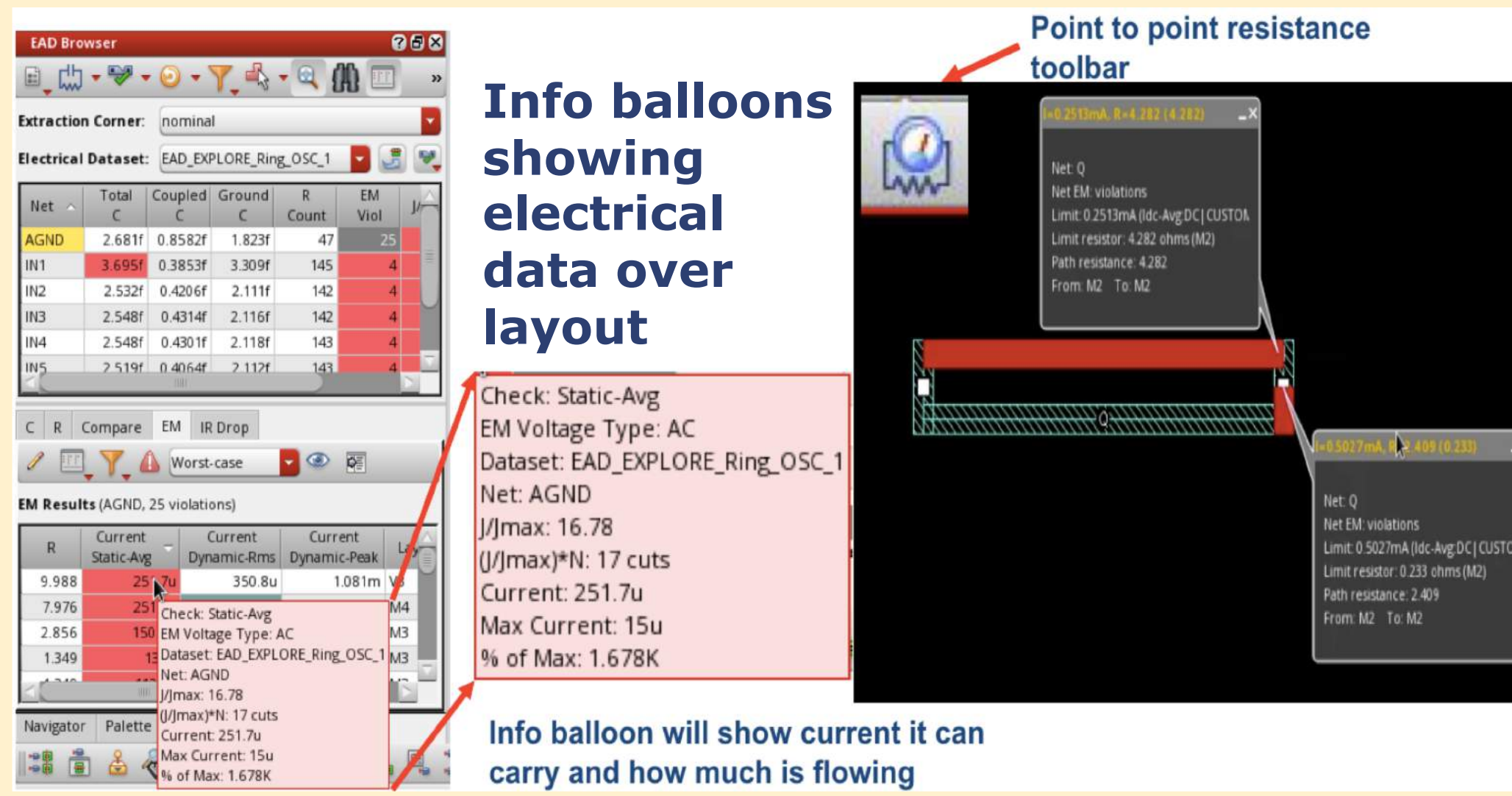
Setting electrical constraints and creating Current Dataset



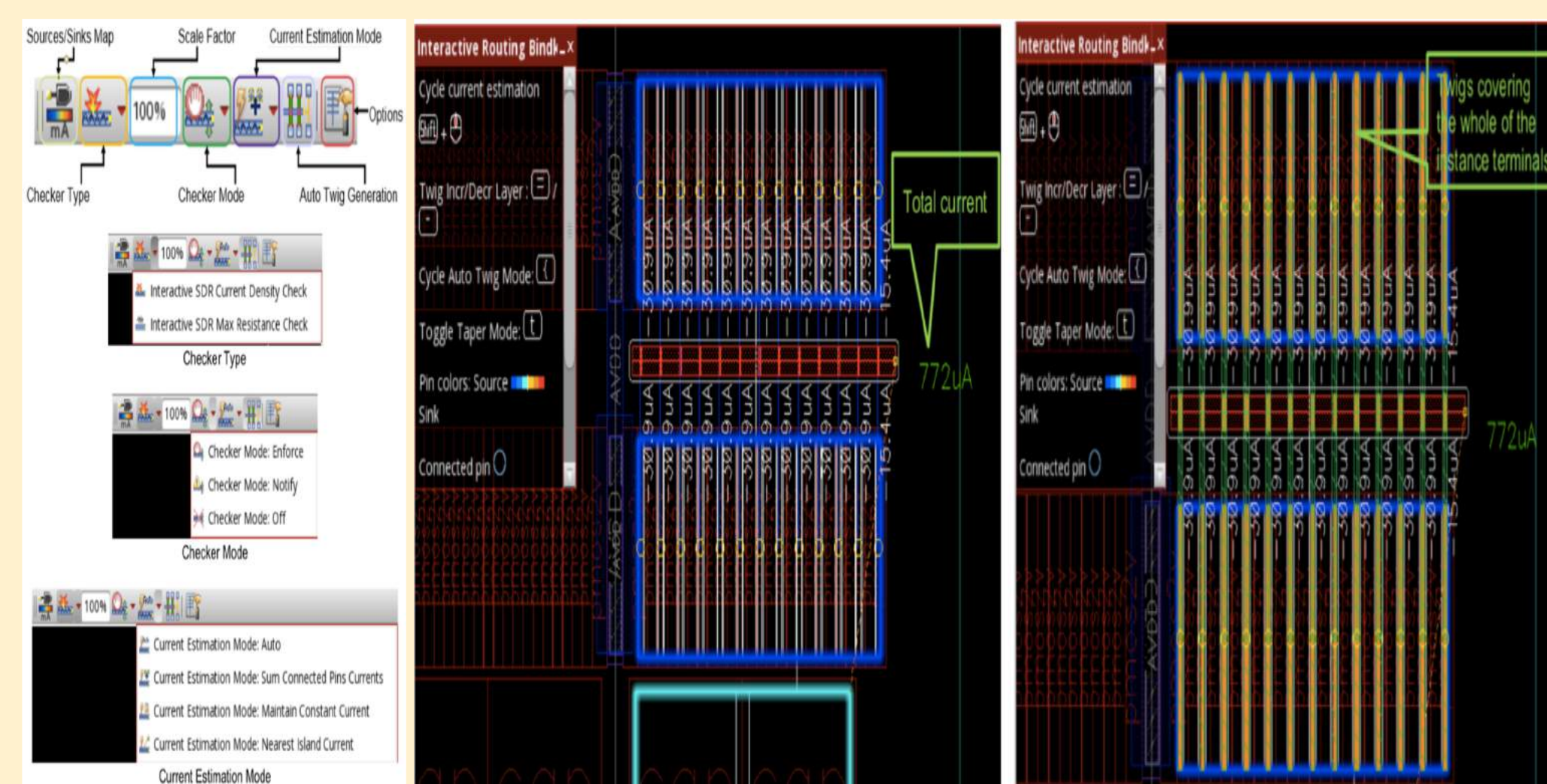
EAD Browser for Navigating & Analysing Parasitics and EM/IR Violations



RESULTS



Simulation Driven Interactive Routing (SDR)



- Guidance of current flow and it's distribution map w.r.t. total current**, shown on layout while interactive routing
- Automatic sizing of wire and vias**
- Automatic connection of twigs with metal and vias**, meeting EM/current density constraints



Real Time Parasitics w.r.t. signoff

Net Name	Sign-off C Extraction	EAD C Extraction	Accuracy
IN1	0.571f	0.556f	3%
IN2	0.574f	0.556f	3%
IN3	0.477f	0.441f	8%

* capacitance results are fast and very close to signoff, which minimizes iterations and gap between schematic and post layout simulation

Net Name	Sign-off R Extraction	EAD R Extraction	Accuracy
IN1	9.17 Ohm	9.56 Ohm	5%
IN2	9.16 Ohm	9.54 Ohm	5%
IN3	9.19 Ohm	9.56 Ohm	5%

* resistance results are fast and very accurate which minimizes iterations and gap between schematic and post layout simulation.

* Results on ST 28FDSOI

CONCLUSION

